

FIG.1A

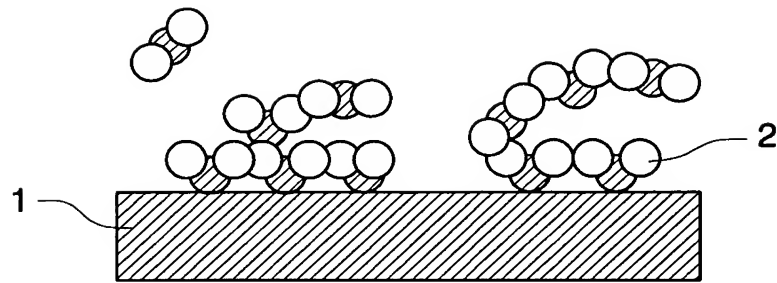


FIG.1B

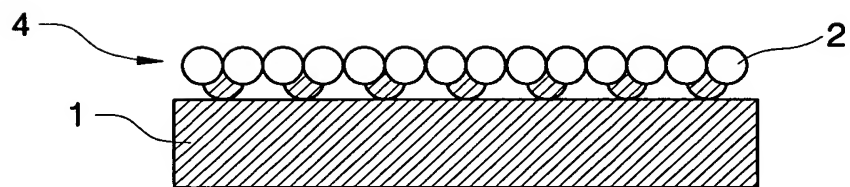


FIG.1C

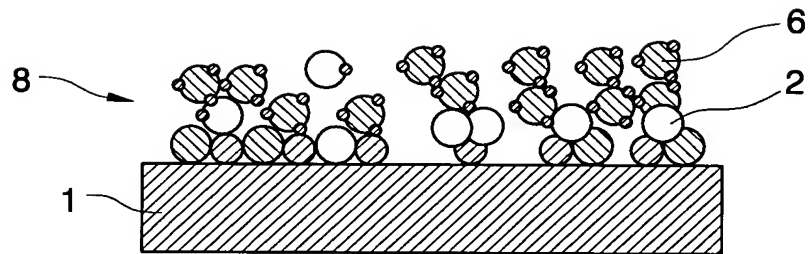


FIG.1D

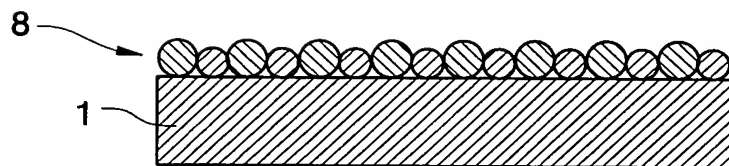


FIG.1E

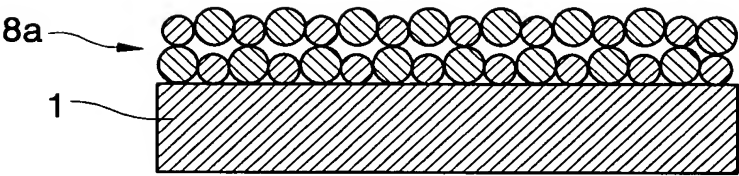


FIG.2

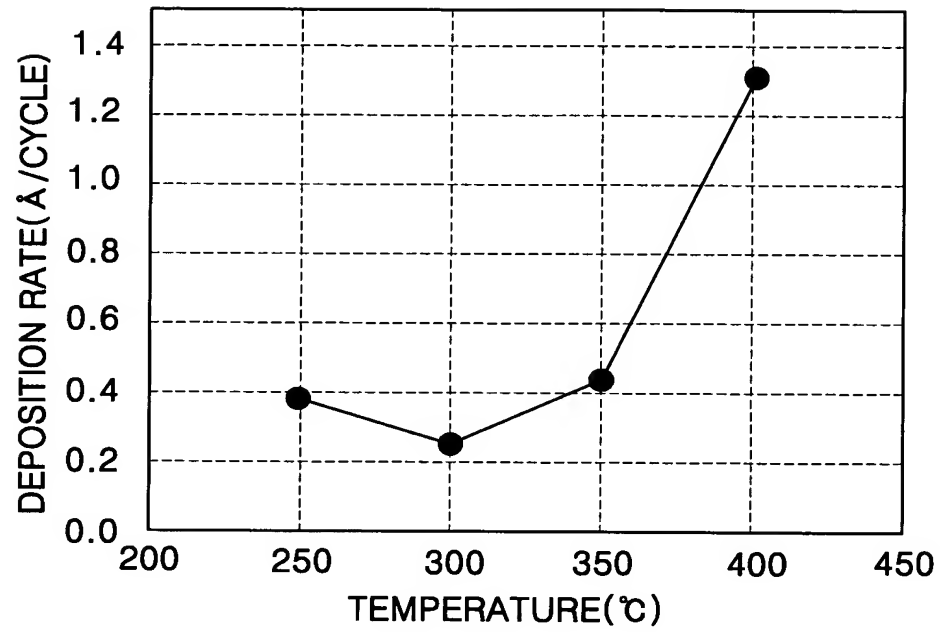


FIG.3

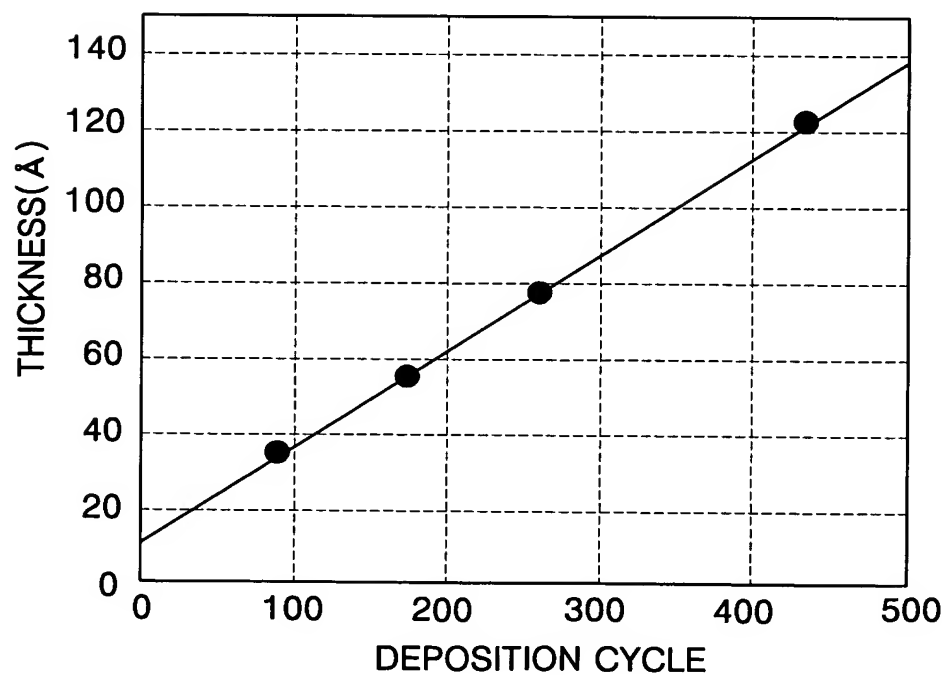


FIG.4A

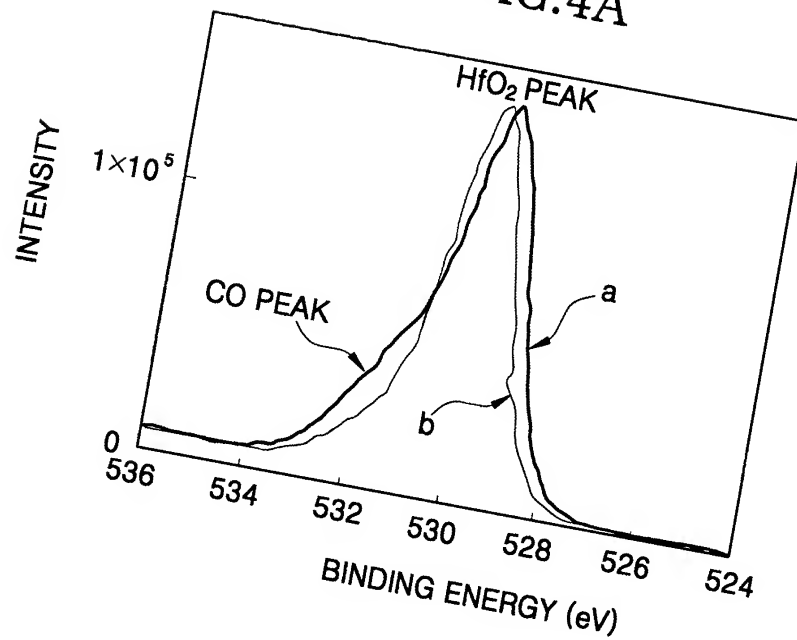


FIG.4B

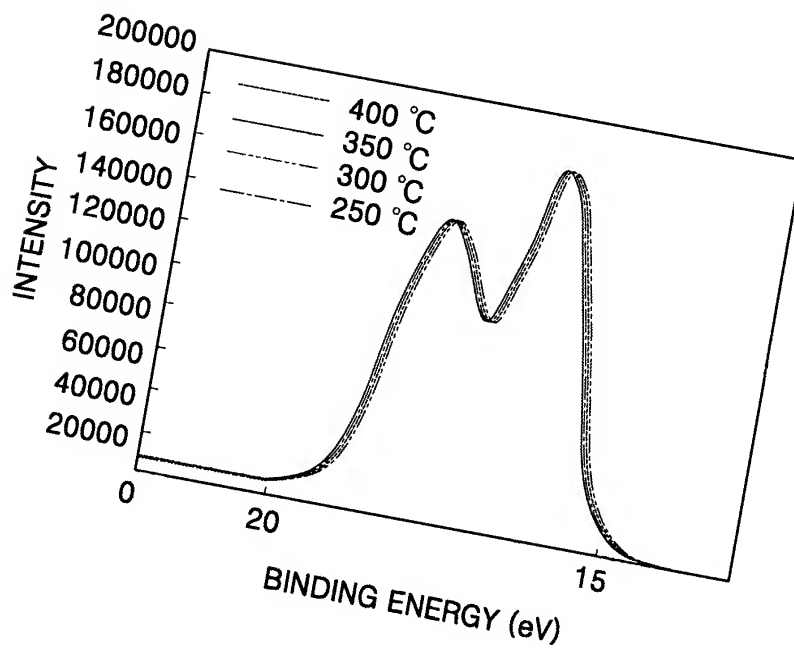
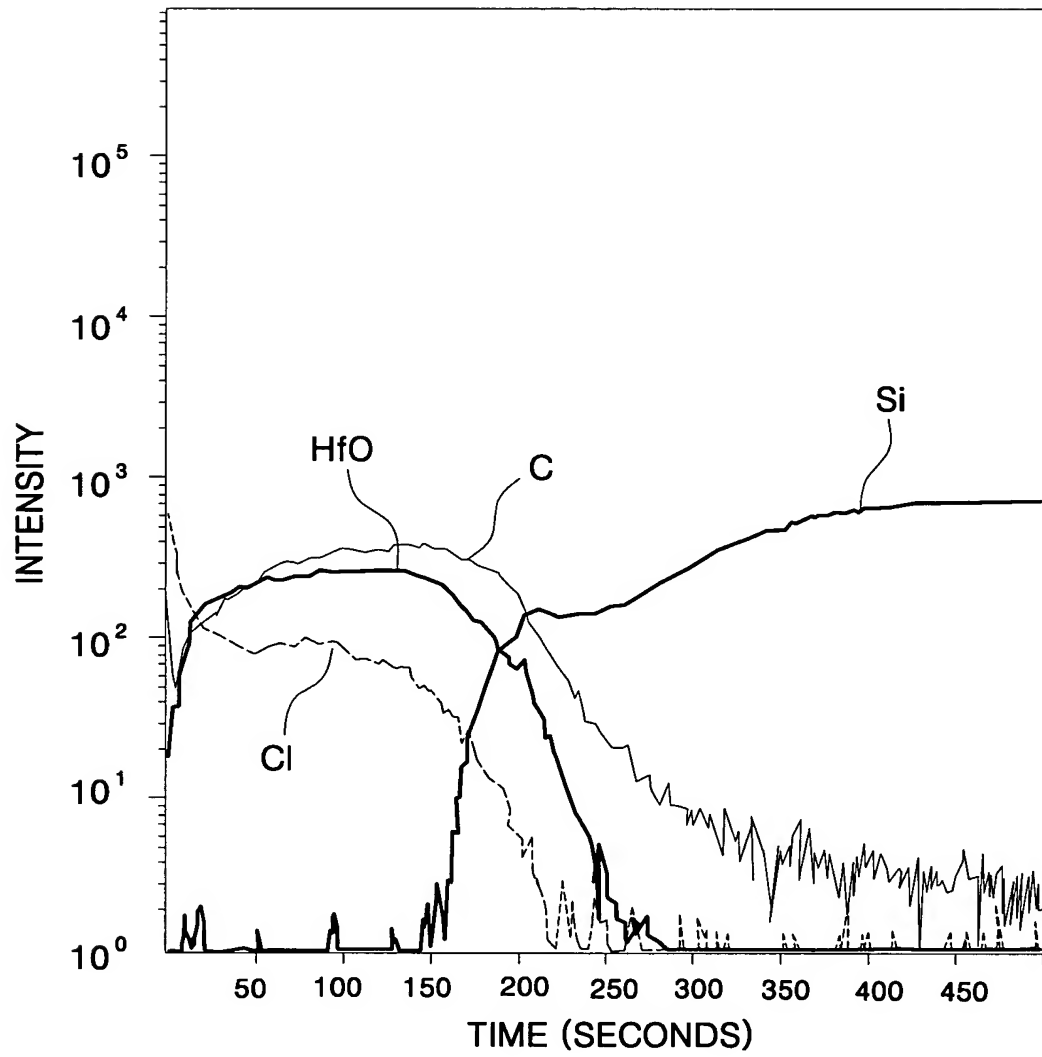


FIG.5

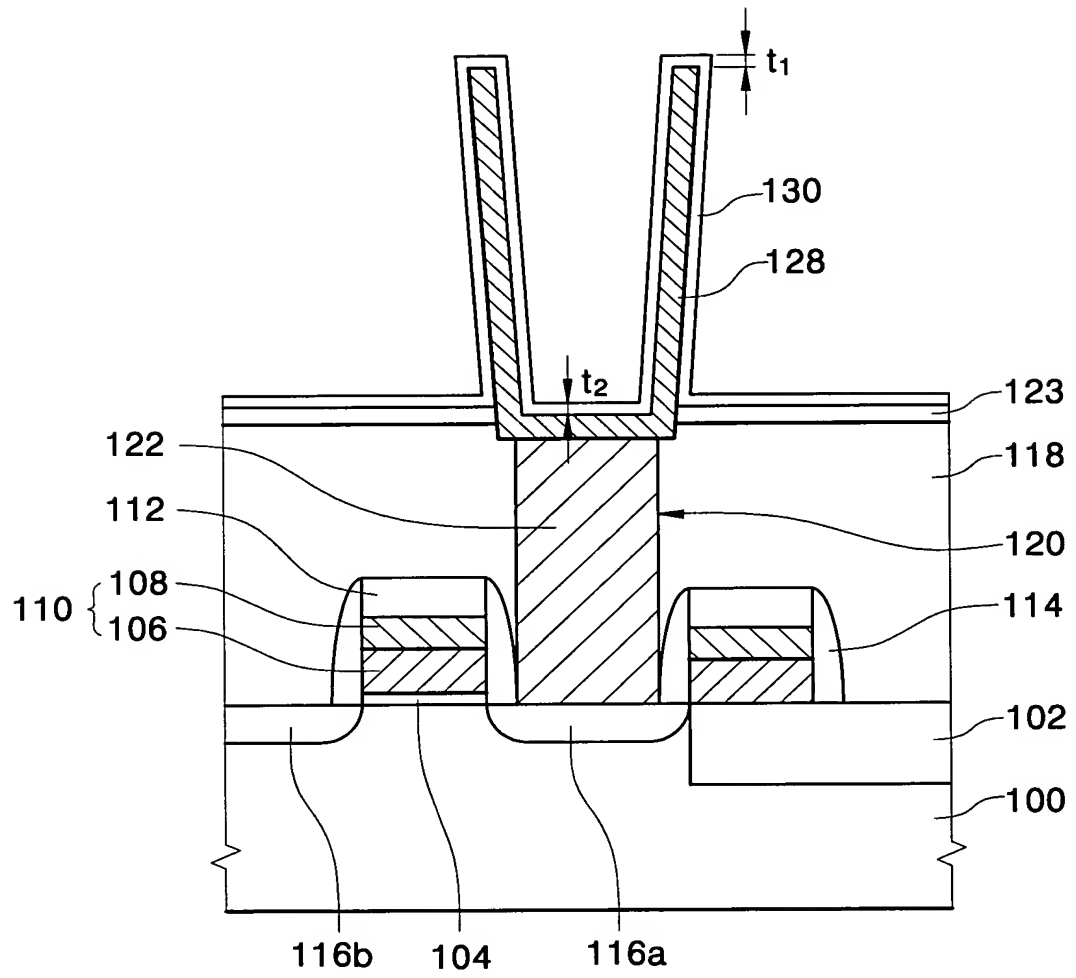


This cross-sectional view shows a semiconductor device structure. A central barrier layer (122) is positioned between two side regions (120). The side regions (120) contain a stack of layers (108, 106) and are surrounded by a material (112). The entire structure is built on a substrate (100) with a layer (102) on top. The central barrier layer (122) is flanked by regions (116a) and (116b). The side regions (120) are flanked by regions (114) and (118). The central barrier layer (122) is flanked by regions (116a) and (116b). The side regions (120) are flanked by regions (114) and (118).

[illegible]



FIG. 6D



[illegible]

FIG.7

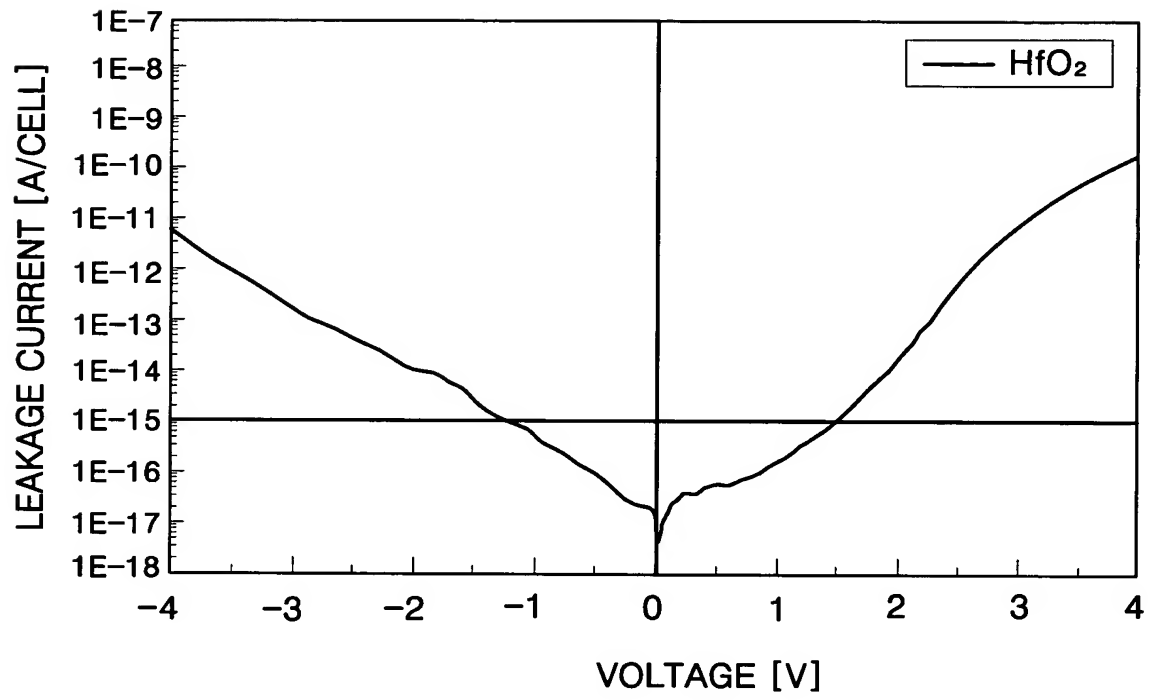


FIG. 8

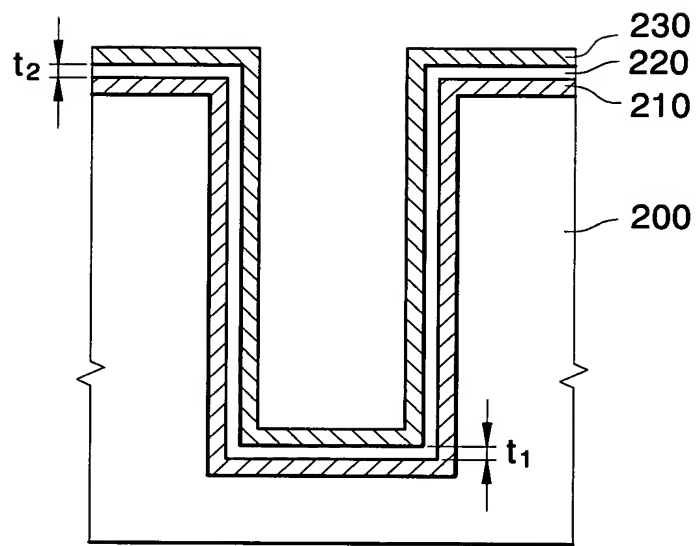


FIG.9A

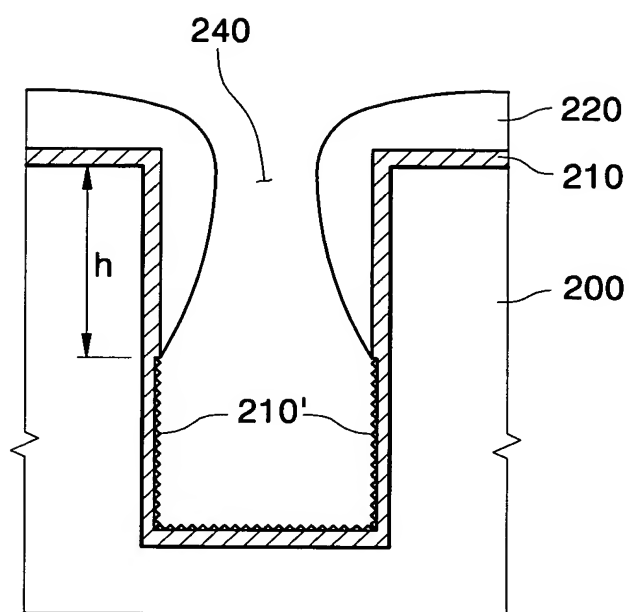


FIG.9B

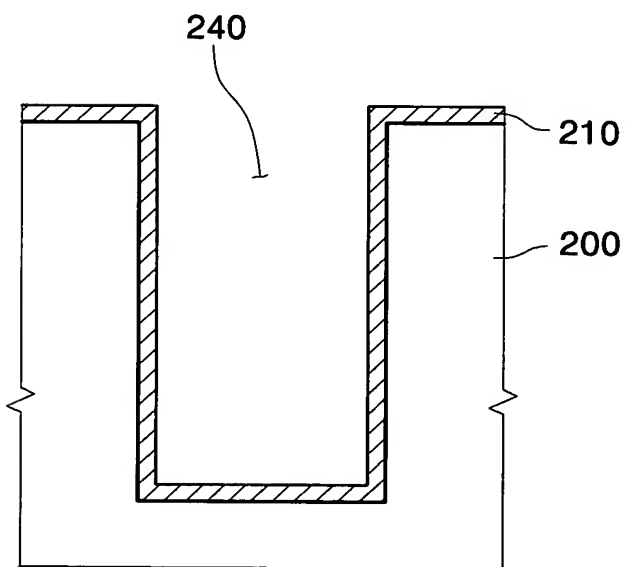


FIG.10

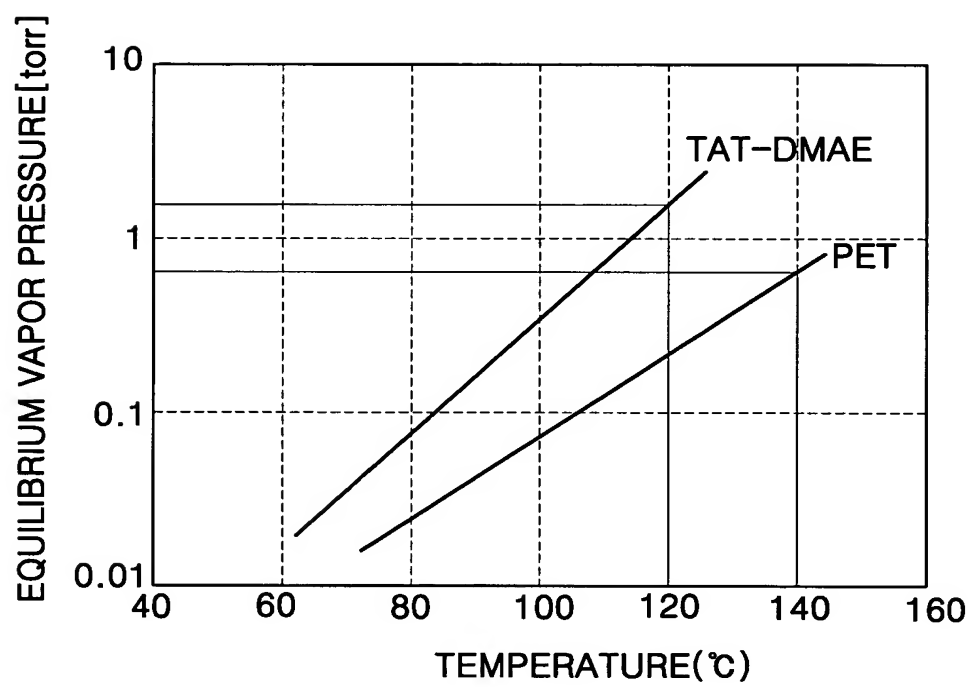


FIG.11

